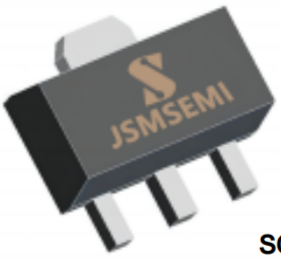
Features

- High Voltage : V_{CEO} = -120V
- High Transition Frequency : f_T = 120MHz(typ.)
- Small Flat Package
- Complementary to 2SC2881



SOT-89

1.BASE

2.COLLECTOR

3.EMITTER

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-120	V
Collector-Base Voltage	V_{CBO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

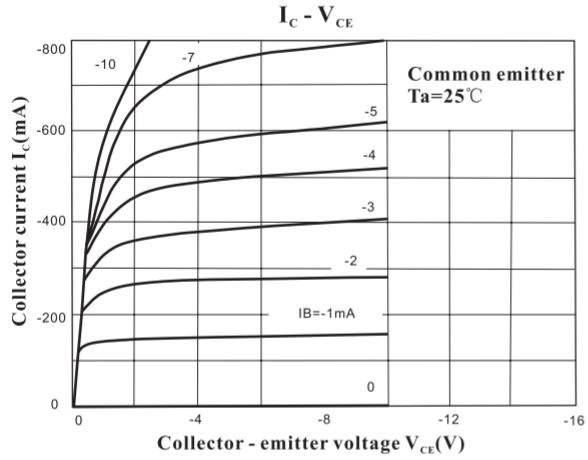
Electrical Characteristics Ta = 25℃

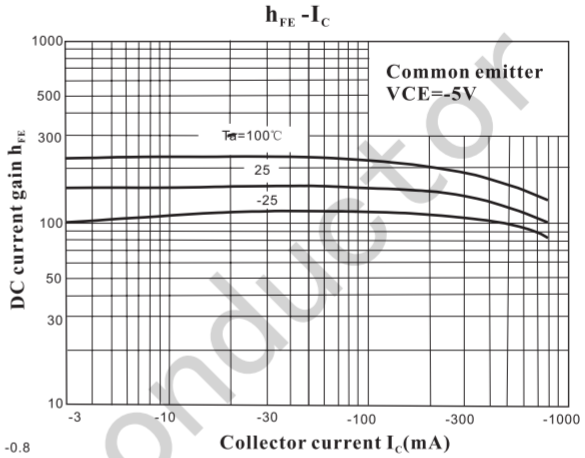
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Emitter Cut-off Current	I_{EBO}	V_{EB} = -5V , I_C = 0			-0.1	μA
Collector Cut-off Current	I_{CBO}	V_{CB} = -120V , I_E = 0			-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -10mA , I_B = 0	-120			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -1mA , I_C = 0	-5			V
DC Current Gain	h_{FE}	V_{CE} = -5V , I_C = -100mA	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -500mA , I_B = -50mA			-1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = -5V , I_C = -500mA			-1.0	V
Transtion Frequency	f_T	V_{CE} = -5V , I_C = -100mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0 , f = 1MHz			30	pF

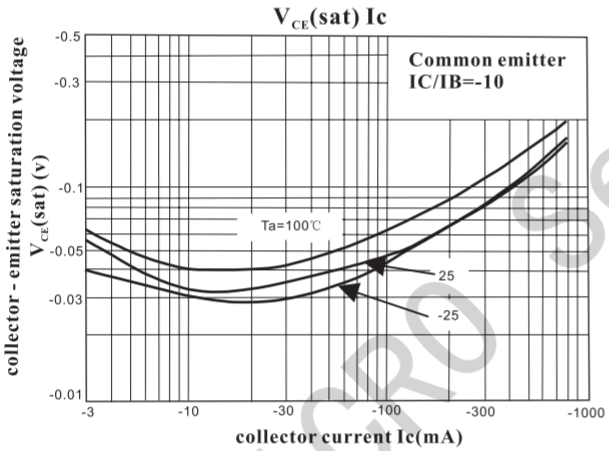
■ hFE Classification

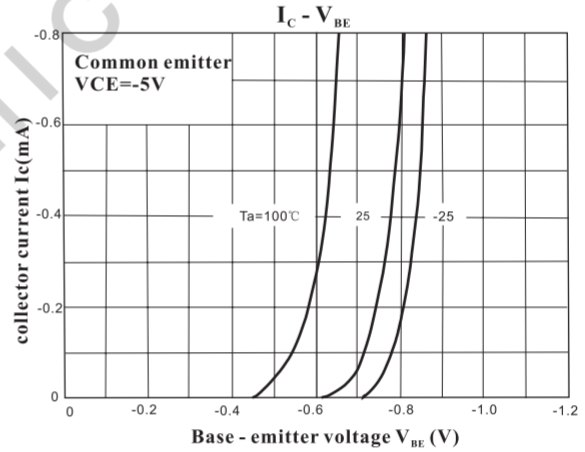
Rank	O	Y
hFE	80～160	120～240

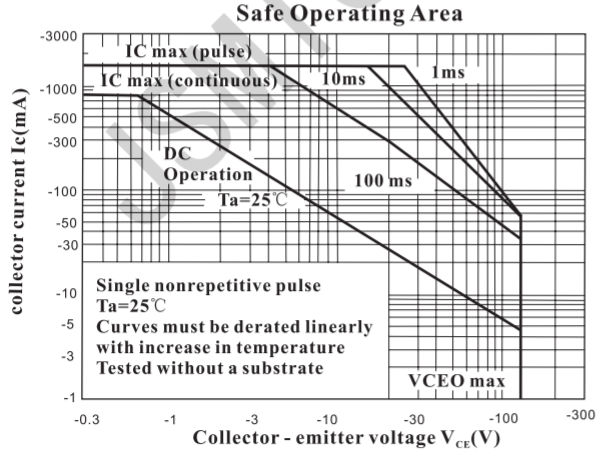
■ Electrical Characteristics Curves

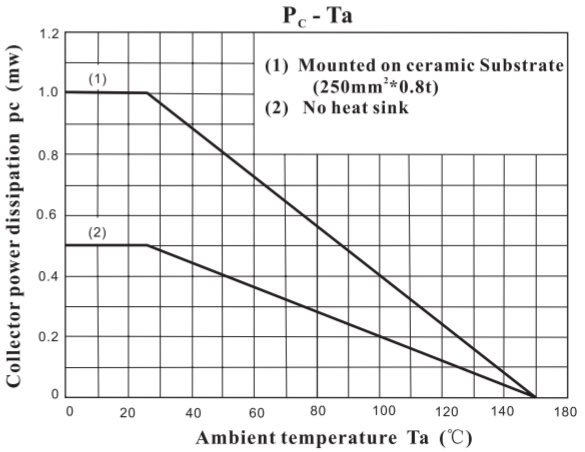












Package Information

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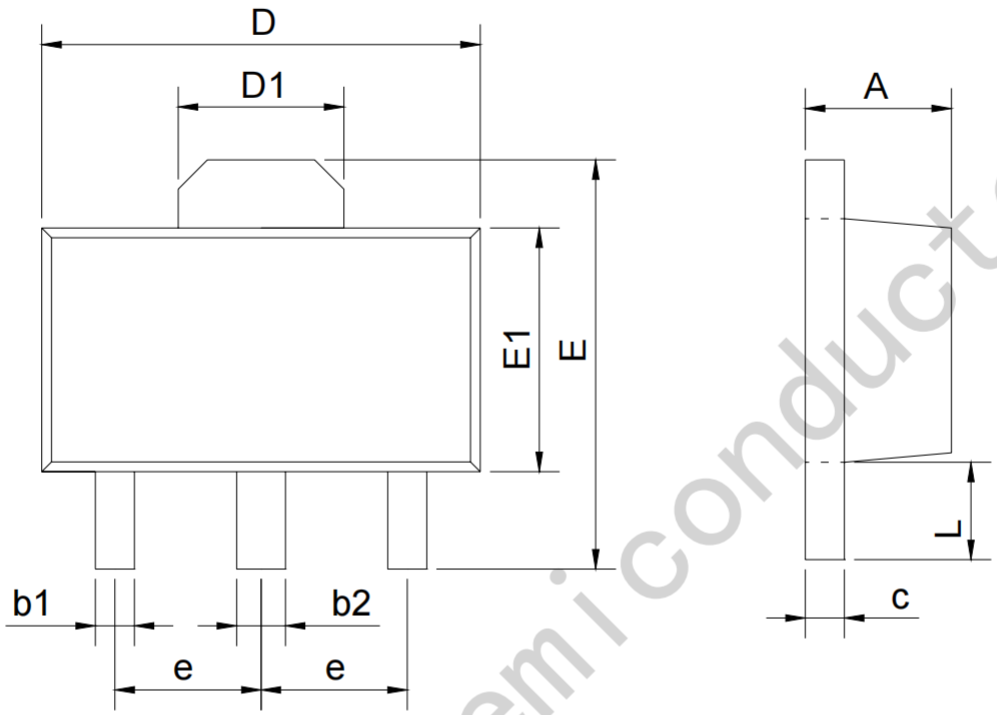

SYMBOL	mm	
	min	max
A	1.40	1.60
b1	0.35	0.50
b2	0.45	0.60
c	0.36	0.46
D	4.30	4.70
D1	1.40	1.80
E	4.00	4.40
E1	2.30	2.70
e	1.50BSC	
L	0.80	1.20